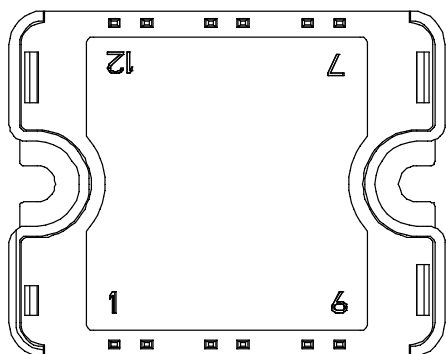
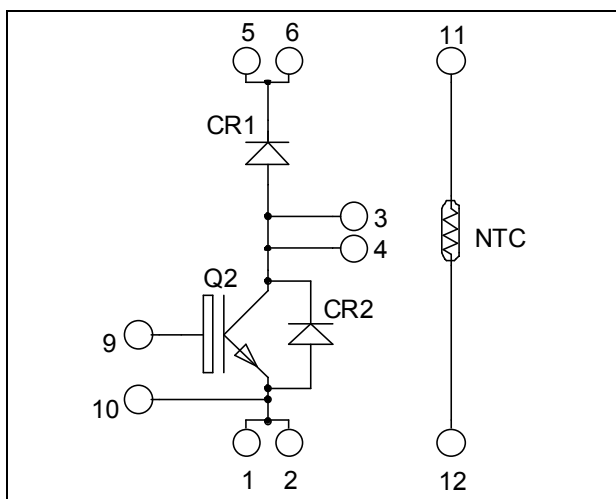


**Boost chopper  
Trench + Field Stop IGBT3  
Power Module**

$$V_{CES} = 600V$$

$$I_C = 150A^* @ T_c = 80^{\circ}C$$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

## Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

## Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

## Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

## Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	600	V
$I_C$	Continuous Collector Current	$T_C = 25^{\circ}C$	225 *
		$T_C = 80^{\circ}C$	150 *
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	350
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	480
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	300A @ 550V

Specification of IGBT device but output current must be limited to 75A to not exceed a delta of temperature greater than 30°C for the connectors.

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified**

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	$\mu A$
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 150A$		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.5 1.7	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5\text{ mA}$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$		9200		pF
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		580		
$C_{res}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		270		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 150A$ $R_G = 3.3\Omega$		115		ns
$T_r$	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			225		
$T_f$	Fall Time			55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $150^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 150A$ $R_G = 3.3\Omega$		130		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			300		
$T_f$	Fall Time			70		
$E_{on}$	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 150A$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	0.85 1.5		mJ
$E_{off}$	Turn off Energy	$R_G = 3.3\Omega$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	4.1 5.3		

**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 600V$			$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	$\mu A$
$I_F$	DC Forward Current			150		A
$V_F$	Diode Forward Voltage	$I_F = 150A$ $V_{GE} = 0V$		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.6 1.5	V
$t_{rr}$	Reverse Recovery Time	$I_F = 150A$ $V_R = 300V$ $di/dt = 3000A/\mu s$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	130 225		ns
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	6.9 14.5		
$E_r$	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.6 3.5		mJ

**Thermal and package characteristics**

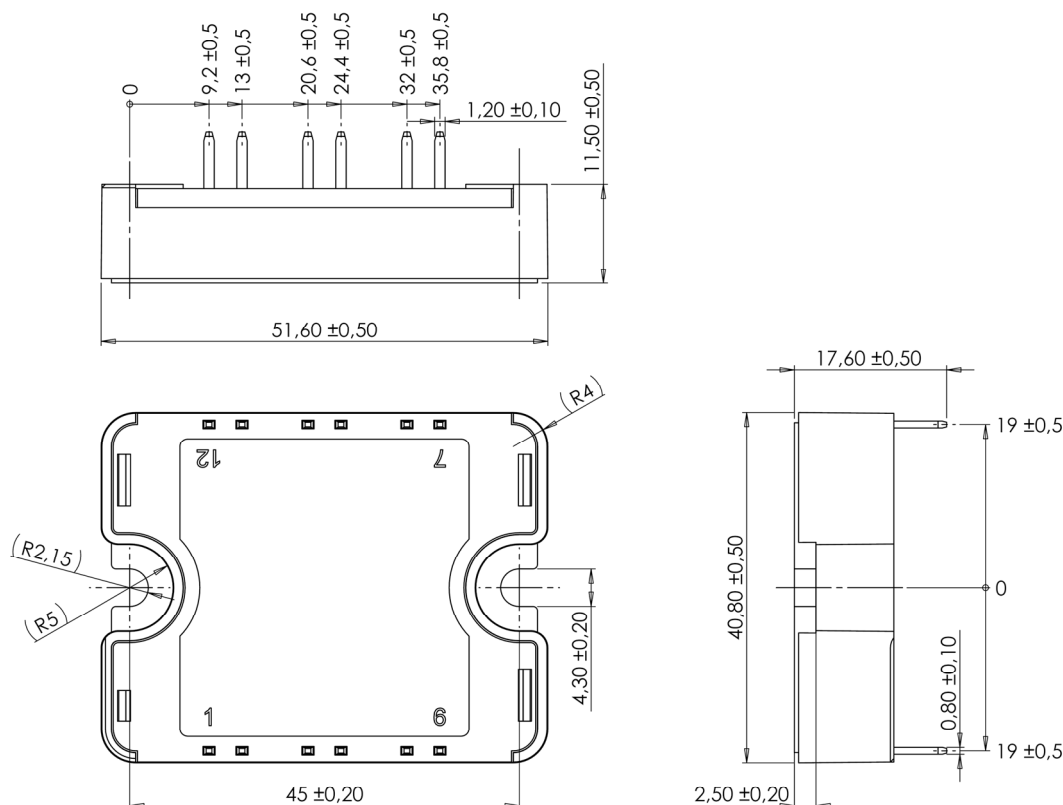
Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.31	°C/W
		Diode		0.52	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V
T <sub>J</sub>	Operating junction temperature range	-40		175	°C
T <sub>STG</sub>	Storage Temperature Range	-40		125	
T <sub>C</sub>	Operating Case Temperature	-40		100	
Torque	Mounting torque	To heatsink	M4	2	N.m
Wt	Package Weight			80	g

**Temperature sensor NTC** (see application note APT0406 on [www.microsemi.com](http://www.microsemi.com) for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

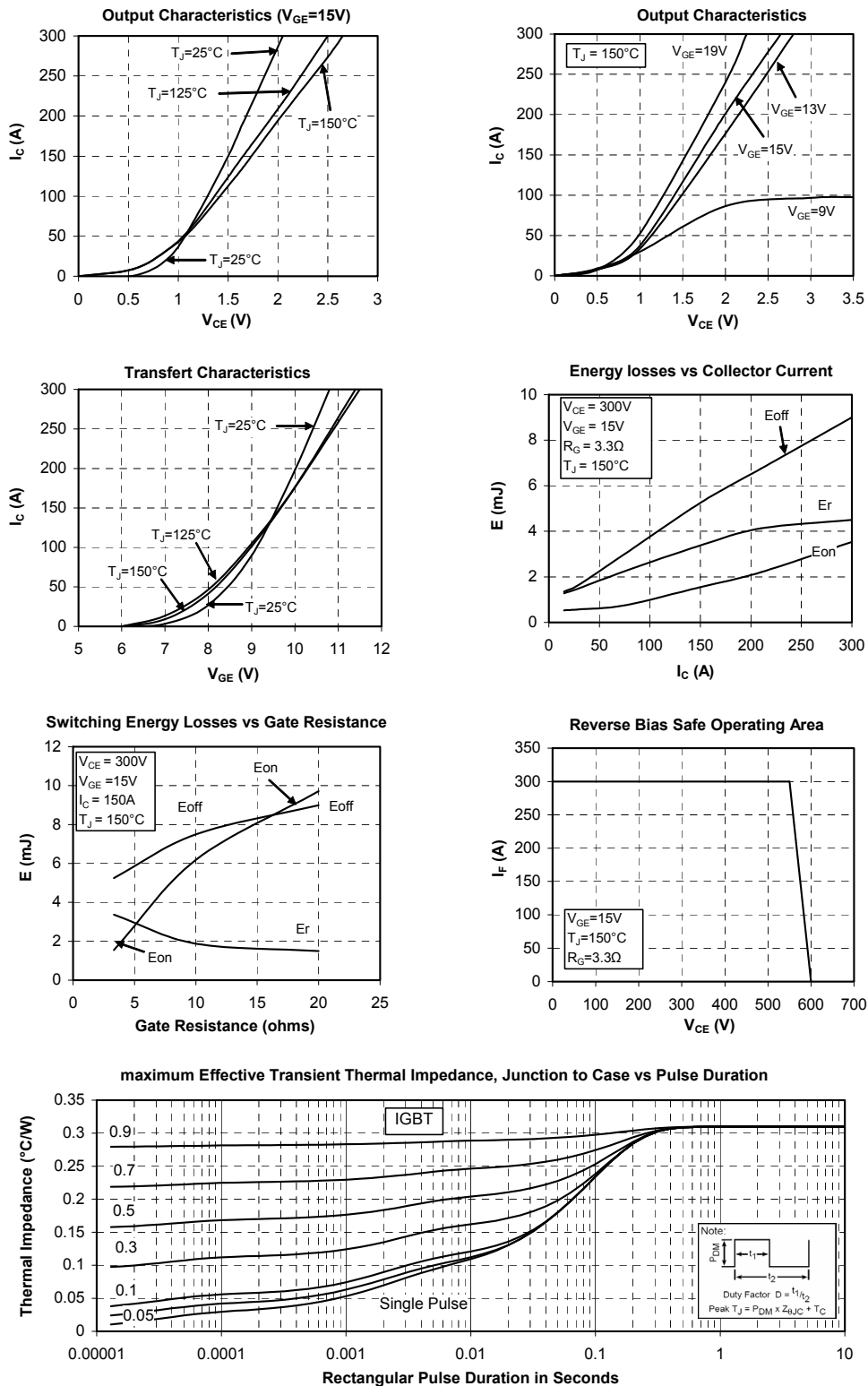
$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

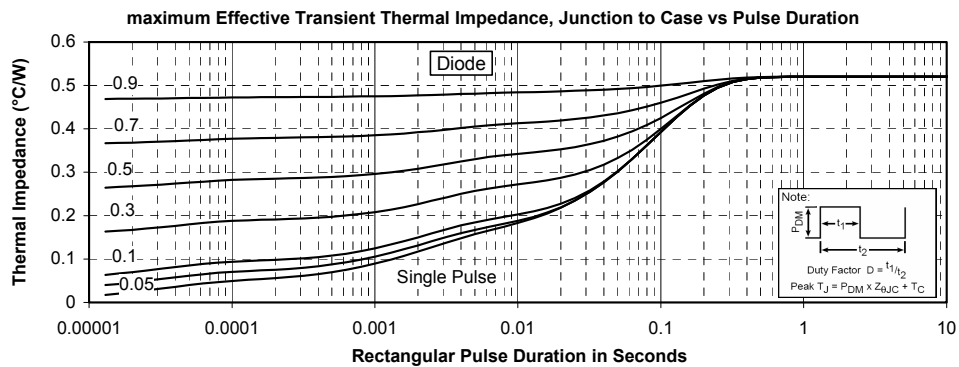
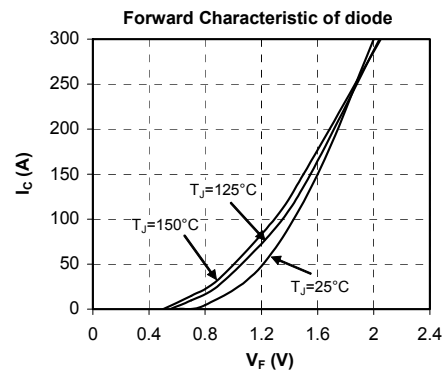
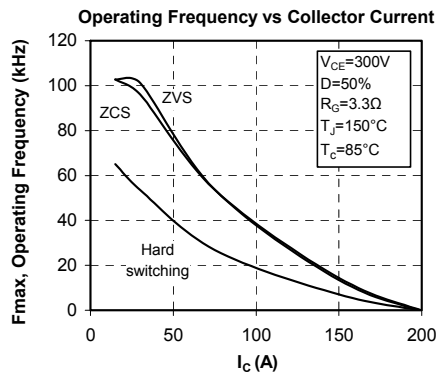
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

**SP1 Package outline** (dimensions in mm)


See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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